# **General Purpose Transistor**

## **PNP Silicon**

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-416/SC-75 which is designed for low power surface mount applications.

#### **Features**

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device



Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	-45	V
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current – Continuous	Ic	-100	mAdc
Collector Current – Peak	Ic	-200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) T <sub>A</sub> = 25°C Derated above 25°C	P <sub>D</sub>	200 1.6	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	600	°C/W
Total Device Dissipation, FR-4 Board (Note 2) T <sub>A</sub> = 25°C Derated above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	400	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

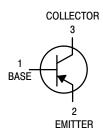
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 @ min pad.
- 2. FR-4 @ 1.0 × 1.0 in pad.



## ON Semiconductor®

#### http://onsemi.com





CASE 463 SOT-416 STYLE 1

#### **MARKING DIAGRAM**



3F = Device Code

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -10 mA)	V <sub>(BR)CEO</sub>	-45	-	-	V	
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -10 µA, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	-50	-	-	V	
Collector – Base Breakdown Voltage (I <sub>C</sub> = –10 μA)	V <sub>(BR)CBO</sub>	-50	-	-	V	
Emitter – Base Breakdown Voltage (I <sub>E</sub> = –1.0 μA)	V <sub>(BR)EBO</sub>	-5.0	_	-	V	
Collector Cutoff Current ( $V_{CB} = -30 \text{ V}$ ) ( $V_{CB} = -30 \text{ V}$ , $T_A = 150^{\circ}\text{C}$ )	I <sub>CBO</sub>	-	_ _	-15 -4.0	nA μA	
ON CHARACTERISTICS	·					
DC Current Gain $(I_C = -10 \mu A, V_{CE} = -5.0 \text{ V})$ $(I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$	h <sub>FE</sub>	- 220	150 290	- 475	-	
Collector – Emitter Saturation Voltage ( $I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$ ) ( $I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$ )	V <sub>CE(sat)</sub>	- -	_ _	-0.3 -0.65	V	
Base – Emitter Saturation Voltage ( $I_C$ = -10 mA, $I_B$ = -0.5 mA) ( $I_C$ = -100 mA, $I_B$ = -5.0 mA)	V <sub>BE(sat)</sub>	- -	-0.7 -0.9	- -	V	
Base – Emitter On Voltage ( $I_C = -2.0$ mA, $V_{CE} = -5.0$ V) ( $I_C = -10$ mA, $V_{CE} = -5.0$ V)	V <sub>BE(on)</sub>	-0.6 -	_ _	-0.75 -0.82	V	
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product (I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	100	_	_	MHz	
Output Capacitance (V <sub>CB</sub> = -10 V, f = 1.0 MHz)	C <sub>ob</sub>	-	-	4.5	pF	
Noise Figure $ \text{(I}_{\text{C}} = -0.2 \text{ mA, V}_{\text{CE}} = -5.0 \text{ Vdc, R}_{\text{S}} = 2.0 \text{ k}\Omega, \\ \text{f} = 1.0 \text{ kHz, BW} = 200 \text{ Hz)} $	NF	-	_	10	dB	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### **TYPICAL CHARACTERISTICS**

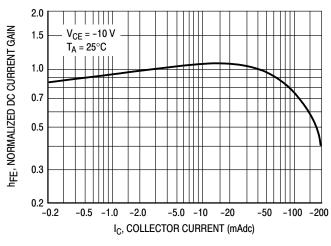


Figure 1. Normalized DC Current Gain

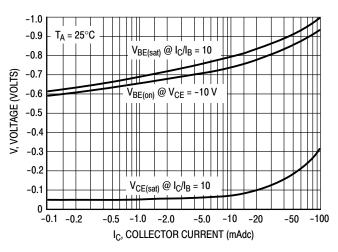


Figure 2. "Saturation" and "On" Voltages

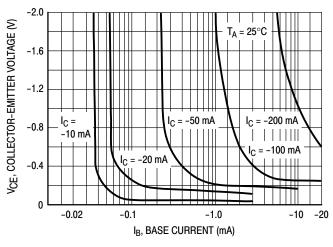


Figure 3. Collector Saturation Region

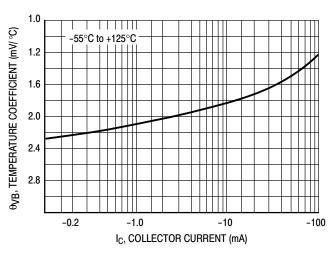


Figure 4. Base-Emitter Temperature Coefficient

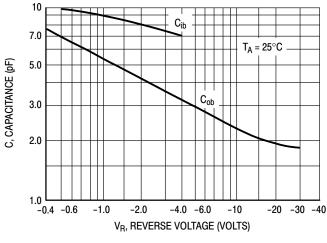


Figure 5. Capacitances

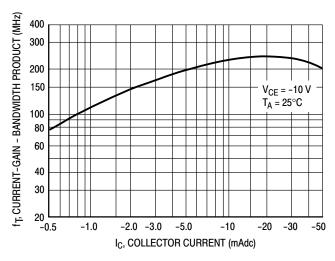


Figure 6. Current-Gain - Bandwidth Product

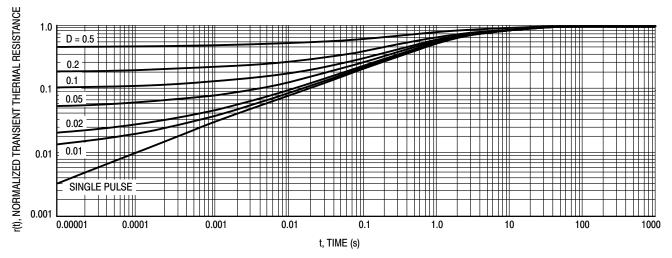


Figure 7. Thermal Response

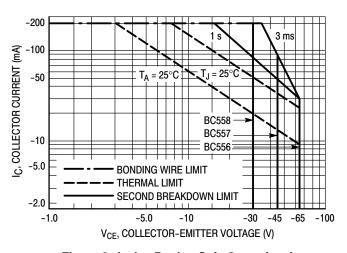


Figure 8. Active Region Safe Operating Area

The safe operating area curves indicate  $I_C$ – $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 8 is based upon  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  or  $T_{A}$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 7. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>	
BC857BTT1G	SOT-416	2 000 / Tana & Baal	
NSVBC857BTT1G*	(PB-Free)	3,000 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

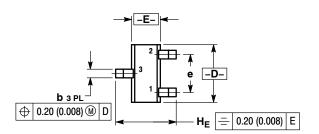
# **MECHANICAL CASE OUTLINE**

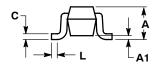




SC-75/SOT-416 CASE 463-01 ISSUE G

**DATE 07 AUG 2015** 





STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

-		MILLIMETERS			INCHES		
L	DIM	MIN	NOM	MAX	MIN	NOM	MAX
	Α	0.70	0.80	0.90	0.027	0.031	0.035
L	A1	0.00	0.05	0.10	0.000	0.002	0.004
	b	0.15	0.20	0.30	0.006	0.008	0.012
	С	0.10	0.15	0.25	0.004	0.006	0.010
	D	1.55	1.60	1.65	0.061	0.063	0.065
	Е	0.70	0.80	0.90	0.027	0.031	0.035
	е	1.00 BSC				0.04 BSC	)
	L	0.10	0.15	0.20	0.004	0.006	0.008
	HE	1.50	1.60	1.70	0.060	0.063	0.067

### **GENERIC MARKING DIAGRAM\***

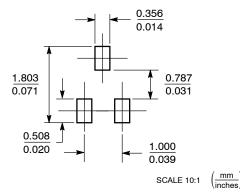


XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Repositor, Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1	

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460

2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA

2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E

US6T6TR 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E UMX21NTR EMT2T2R MCH6102-TL-E FP204-TL-E

NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13

NTE15 NTE16001